

# XN06435 (XN6435)

## Silicon PNP epitaxial planar type

For high-frequency amplification

### ■ Features

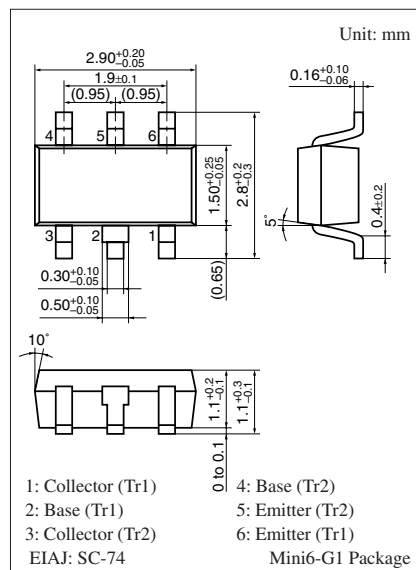
- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- 2SA1022 × 2

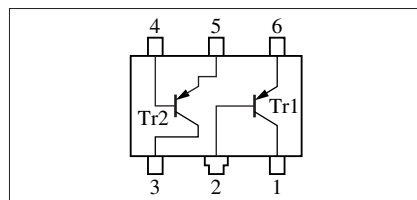
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-30	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-20	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-30	mA
Total power dissipation	$P_T$	300	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 7W

Internal Connection



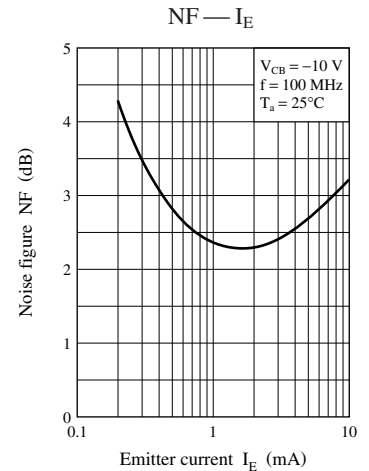
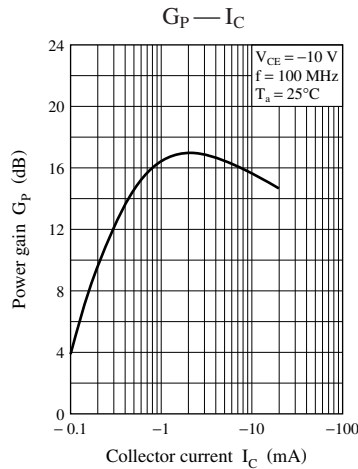
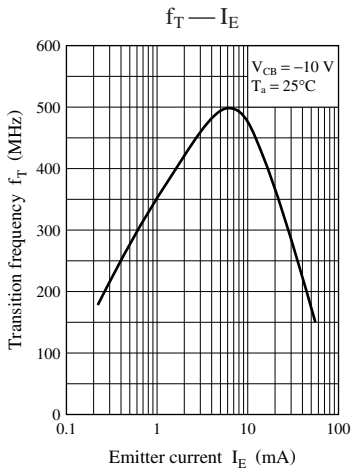
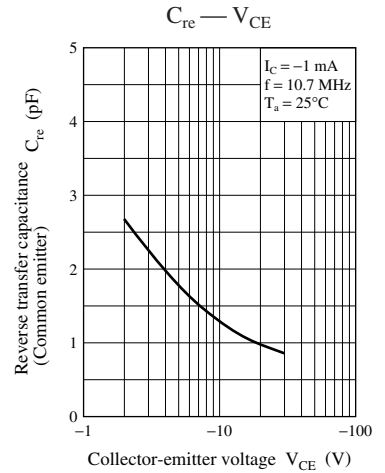
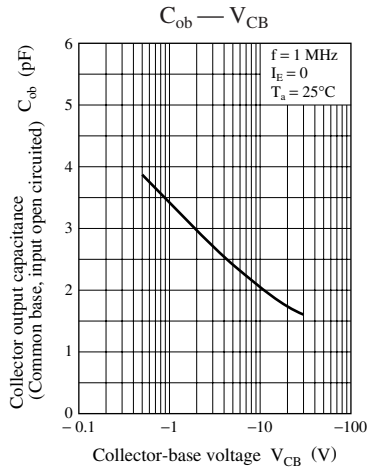
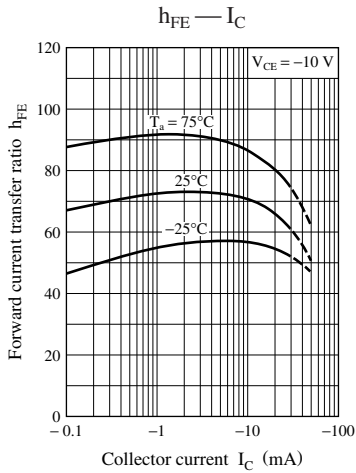
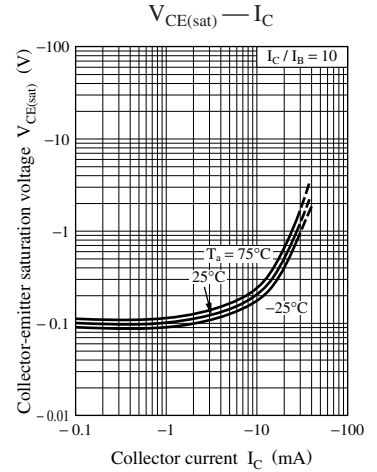
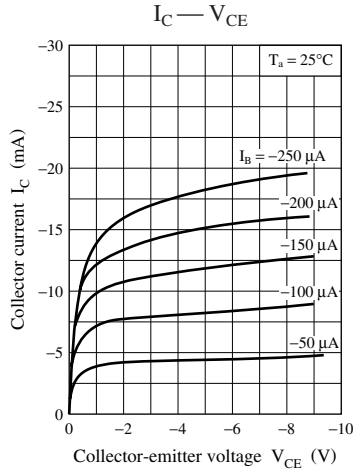
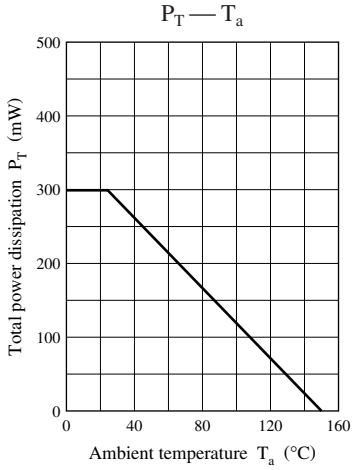
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Base-emitter voltage	$V_{BE}$	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}$		-0.7		V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -10\text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -20\text{ V}, I_B = 0$			-100	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$			-10	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}$	50		220	—
$h_{FE}$ ratio *	$h_{FE(\text{Small})}$ $/I_{\text{Large}}$	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}$	0.50	0.99		—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$		-0.1		V
Transition frequency	$f_T$	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 200\text{ MHz}$	150			MHz
Noise figure	NF	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 5\text{ MHz}$		2.8		dB
Reverse transfer impedance	$Z_{rb}$	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 2\text{ MHz}$		22		$\Omega$
Reverse transfer capacitance (Common emitter)	$C_{re}$	$V_{CE} = -10\text{ V}, I_E = 1\text{ mA}, f = 10.7\text{ MHz}$		1.2		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.



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